

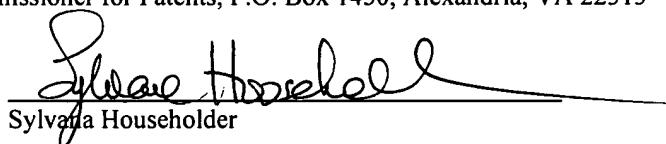
DOCKET NO: S1432-700819

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Narendar et al.
Serial No: 10/752,434
Confirmation No: 3742
Filed: January 6, 2004
For: HIGH PURITY SILICON CARBIDE ARTICLES
AND METHODS
Examiner: Karl E. Group
Art Unit: 1755

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

The undersigned hereby certifies that this document is being placed in the United States mail with first-class postage attached, addressed to Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the 28 day of December, 2005.



Sylvana Householder

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT FILED PURSUANT TO THE DUTY OF
DISCLOSURE UNDER 37 CFR §§1.56, 1.97 AND 1.98

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. §§1.56, 1.97 and 1.98, the Applicant requests consideration of this Information Disclosure Statement.

PART I: Compliance with 37 C.F.R. §1.97

This Information Disclosure Statement has been filed before the mailing of a first Office Action after the filing of a request for continued examination under 37 C.F.R. §1.114.

No fee or certification is required.

PART II: Information Cited

The Applicant hereby makes of record in the above-identified application the information listed on the attached form PTO-1449 (modified). The order of presentation of the references should not be construed as an indication of the importance of the references.

The Applicant hereby makes the following additional information of record in the above-identified application.

The Applicant would like to bring to the Examiner's attention the enclosed partial search report from a corresponding International or Foreign National Application PCT/US2005/000183.

The applicant would like to bring to the Examiner's attention the following co-pending applications that may contain subject matter related to this application:

<u>Serial No.</u>	<u>Filing Date</u>	<u>Inventor(s)</u>
10/752,480	January 6, 2004	Richard F. Buckley et al.

PART III: Explanation of Non-English Language References and Remarks Concerning Other Information Cited

The following is a concise explanation of the relevance of each non-English language reference listed on the attached form PTO-1449 (modified):

JP 2002 338366 appears to be directed to a high purity silicon carbide heating element and method of producing the same. An English Abstract is enclosed.

The following are remarks concerning the other information cited:

PART IV: Remarks

Documents cited anywhere in the Information Disclosure Statement are enclosed unless otherwise indicated. It is respectfully requested that:

1. The Examiner consider completely the cited information, along with any other information, in reaching a determination concerning the patentability of the present claims;
2. The enclosed form PTO-1449 be signed by the Examiner to evidence that the cited information has been fully considered by the Patent and Trademark Office during the examination of this application;

3. The citations for the information be printed on any patent which issues from this application.

By submitting this Information Disclosure Statement, the Applicant makes no representation that a search has been performed, of the extent of any search performed, or that more relevant information does not exist.

By submitting this Information Disclosure Statement, the Applicant makes no representation that the information cited in the Statement is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b).

By submitting this Information Disclosure Statement, the Applicant makes no representation that the information cited in the Statement is, or is considered to be, in fact, prior art as defined by 35 U.S.C. §102.

Notwithstanding any statements by the Applicant, the Examiner is urged to form his own conclusion regarding the relevance of the cited information.

An early and favorable action is hereby requested.

Respectfully submitted,
Narendar et al., Applicant

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Date: December 27, 2005



FORM PTO-1449/A and B (Modified) INFORMATION DISCLOSURE STATEMENT BY APPLICANT				APPLICATION NO.: 10/752,434	ATTY. DOCKET NO.: S1432-700819		
				FILING DATE: January 6, 2004	CONFIRMATION NO.: 3742		
				APPLICANT: Narendar et al.			
				GROUP ART UNIT: 1755	EXAMINER: Karl E. Group		
Sheet	1	of	1				

U.S. PATENT DOCUMENTS

Examiner's Initials	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication or of issue of Cited Document MM-DD-YYYY
		Number	Kind Code		
		*5,834,387		Divakar et al.	11-10-1998

FOREIGN PATENT DOCUMENTS

Examiner's Initials	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document (not necessary)	Date of Publication of Cited Document MM-DD-YYYY	Translation (Y/N)
		Office/ Country	Number	Kind Code			
		EP	1 184 355	A1	Toshiba Ceramics Co., Ltd.	03-06-2002	
		JP	2002 338366	A	Tokai Konetsu Kogyo Co., Ltd.	11-27-2002	Abstract
		CA	2 466 183	A1	Bridgestone Corporation, JP	05-15-2003	

OTHER ART — NON PATENT LITERATURE DOCUMENTS

Examiner's Initials	Cite No	Include name of the author (in CAPITAL LETTERS) title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, relevant page(s), volume-issue number(s), publisher, city and/or country where published.	Translation (Y/N)
		H. RAUH, "Atlas for Characterization of Defects in Silicon," Wacker Siltronic AG, Burghausen, Germany, pp. 1-64, 2004.	
		R. F. BUCKLEY et al., "Design and Analysis of a Semiconductor Wafer Processing System for 30 mm Wafers," MS Thesis submitted to the Worcester Polytechnic Institute, 12/22/99, pp. i-62.	
		B. LEROY et al., "Warpage of Silicon Wafers," <i>Journal Electrochemical Society</i> , Vol. 127, No. 4, April 1980, pp. 961-970.	
		M. SCHREMS et al., "Simulation of Temperature Distributions During Fast Thermal Processing," <i>Journal Electrochemical Society</i> , Semiconductor Silicon 1994, pp. 1050-1059.	
		NILSON et al., "Scaling wafer stresses and thermal processes to large wafers," <i>Thin Solid Films</i> 315, 1998, pp. 286-293.	
		PETER VAN ZANT, "Microchip Fabrication: A Practical Guide to Semiconductor Processing," McGraw Hill, Fourth Edition, 1990, chapters 3-7.	
		SHIGLEY et al., "Mechanical Engineering Design," McGraw Hill, copyright 1989, p. 62, p. 159.	
		Machinery Handbook, 24 th Edition, Industrial Press, Copyright 1992, pp. 1598-1603.	

EXAMINER	DATE CONSIDERED

#EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*a copy of this reference is not provided because a copy of this reference need not be provided as the reference is a published U.S. Patent or U.S. Patent application and the present application was filed after June 30, 2003.